

General Description

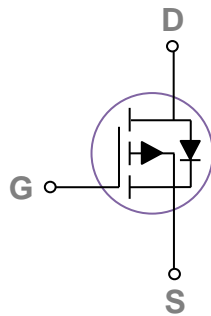
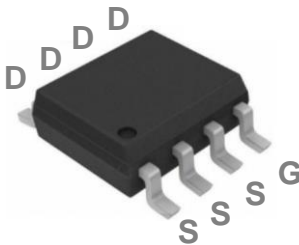
These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	RDSON	ID
-100V	42mΩ	-4.5A

Features

- -100V,-4.5A, $R_{DS(ON)} 42m\Omega @ V_{GS} = -10V$
- Improved dv/dt capability
- Fast switching
- Green Device Available

SOP8 Pin Configuration



Applications

- Networking
- Load Switch
- LED applications

Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	-100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current – Continuous (T _A =25°C)	-4.5	A
	Drain Current – Continuous (T _A =70°C)	-3.6	A
I _{DM}	Drain Current – Pulsed ¹	-18	A
EAS	Single Pulse Avalanche Energy ²	180	mJ
IAS	Single Pulse Avalanche Current ²	-60	A
P _D	Power Dissipation (T _A =25°C)	2	W
	Power Dissipation – Derate above 25°C	0.016	W/°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to ambient	---	62.5	°C/W

Electrical Characteristics (T_J=25 °C, unless otherwise noted)
Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-100	---	---	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-100V, V _{GS} =0V, T _J =25°C	---	---	-1	uA
		V _{DS} =-80V, V _{GS} =0V, T _J =125°C	---	---	-10	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA

On Characteristics

R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-10V, I _D =-2A	---	35	42	mΩ
		V _{GS} =-4.5V, I _D =-1.5A	---	38	49	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.2	-1.6	-2.5	V

Dynamic and switching Characteristics

Q _g	Total Gate Charge ^{3, 4}	V _{DS} =-50V, V _{GS} =-10V, I _D =-2A	---	92	140	nC
Q _{gs}	Gate-Source Charge ^{3, 4}		---	13	20	
Q _{gd}	Gate-Drain Charge ^{3, 4}		---	14	20	
T _{d(on)}	Turn-On Delay Time ^{3, 4}	V _{DD} =-50V, V _{GS} =-10V, R _G =6Ω I _D =-2A	---	10	15	ns
T _r	Rise Time ^{3, 4}		---	15	25	
T _{d(off)}	Turn-Off Delay Time ^{3, 4}		---	20	30	
T _f	Fall Time ^{3, 4}		---	25	40	
C _{iss}	Input Capacitance	V _{DS} =-50V, V _{GS} =0V, F=1MHz	---	5700	8550	pF
C _{oss}	Output Capacitance		---	160	240	
C _{rss}	Reverse Transfer Capacitance		---	120	180	
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	---	4.7	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current	V _G =V _D =0V, Force Current	---	---	-4.5	A
I _{SM}	Pulsed Source Current		---	---	-9	A
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =-1A, T _J =25°C	---	---	-1	V
t _{rr}	Reverse Recovery Time	V _R =-50V, I _S =-2A	---	55	---	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs, T _J =25°C	---	60	---	nC

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. V_{DD}=-50V, V_{GS}=-10V, L=0.1mH, I_{AS}=-60A., R_G=25Ω, Starting T_J=25°C.
3. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%.
4. Essentially independent of operating temperature.

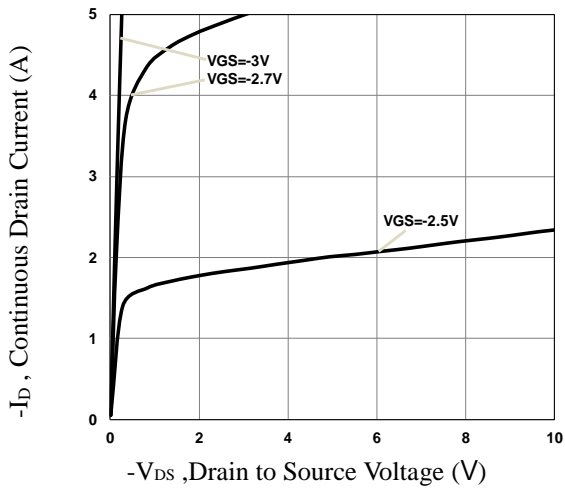


Fig.1 Typical Output Characteristics

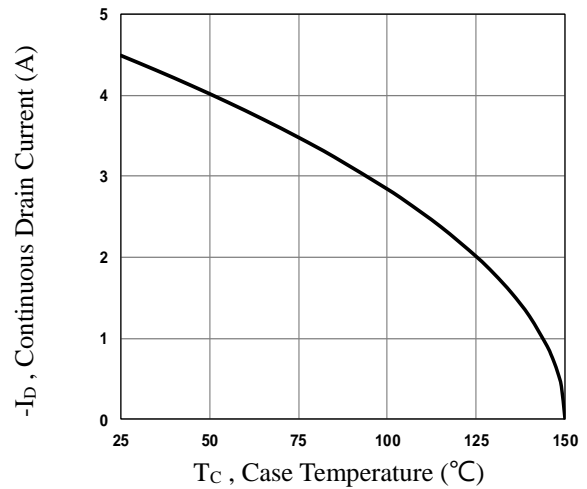


Fig.2 Continuous Drain Current vs. T_c

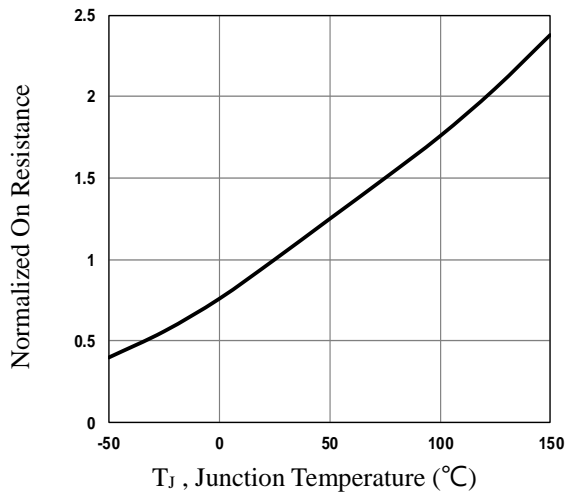


Fig.3 Normalized R_{DS(on)} vs. T_j

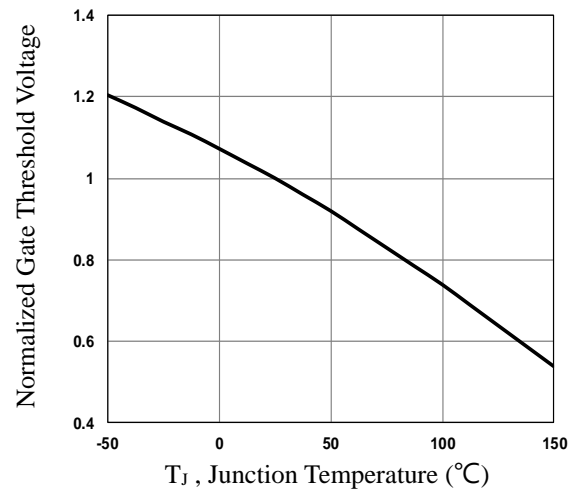


Fig.4 Normalized V_{th} vs. T_j

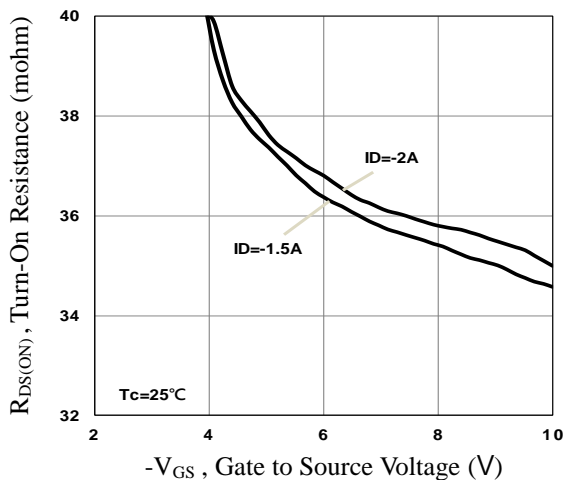


Fig.5 Turn-On Resistance vs. V_{GS}

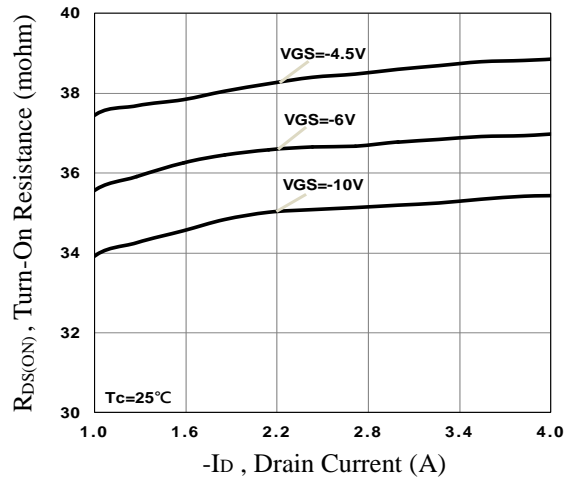


Fig.6 Turn-On Resistance vs. I_D

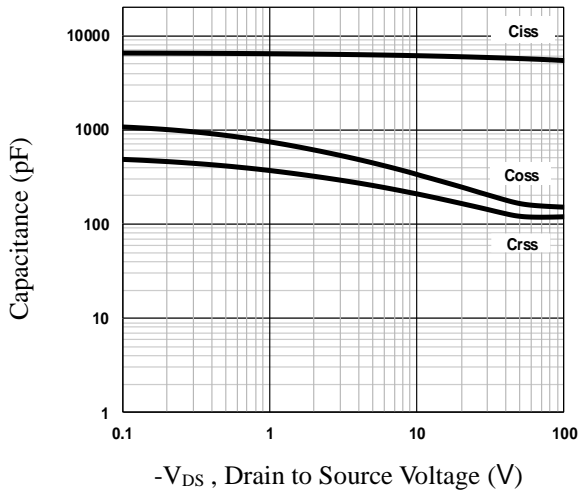


Fig.7 Capacitance Characteristics

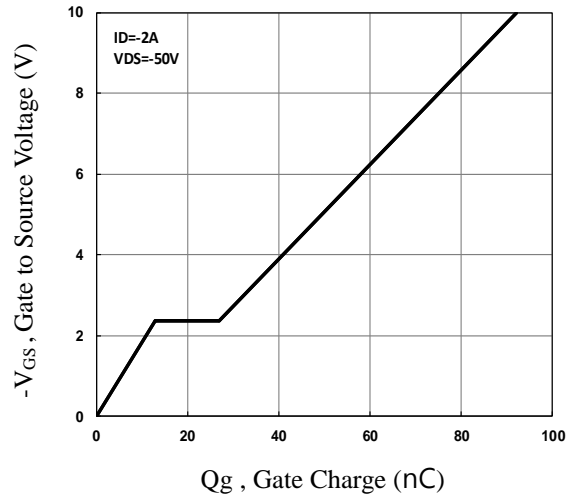


Fig.8 Gate Charge Characteristics

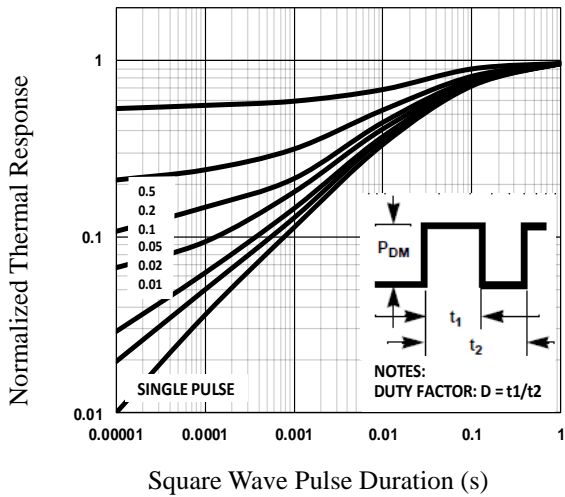


Fig.9 Normalized Transient Impedance

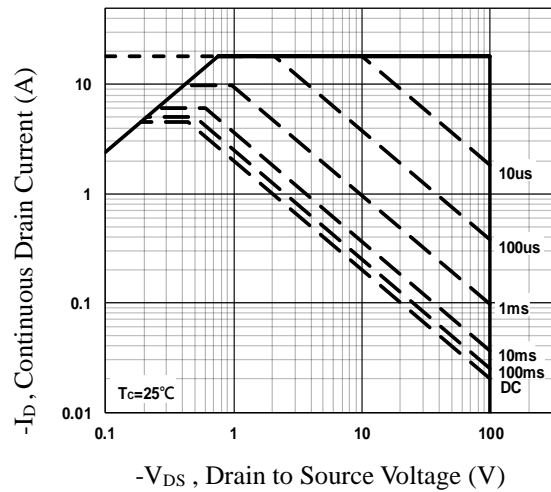


Fig.10 Maximum Safe Operation Area

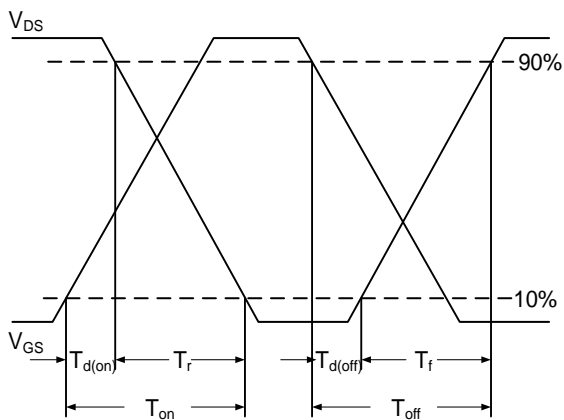


Fig.11 Switching Time Waveform

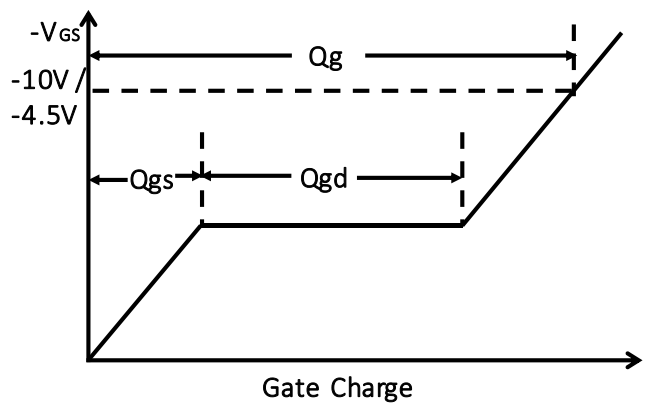
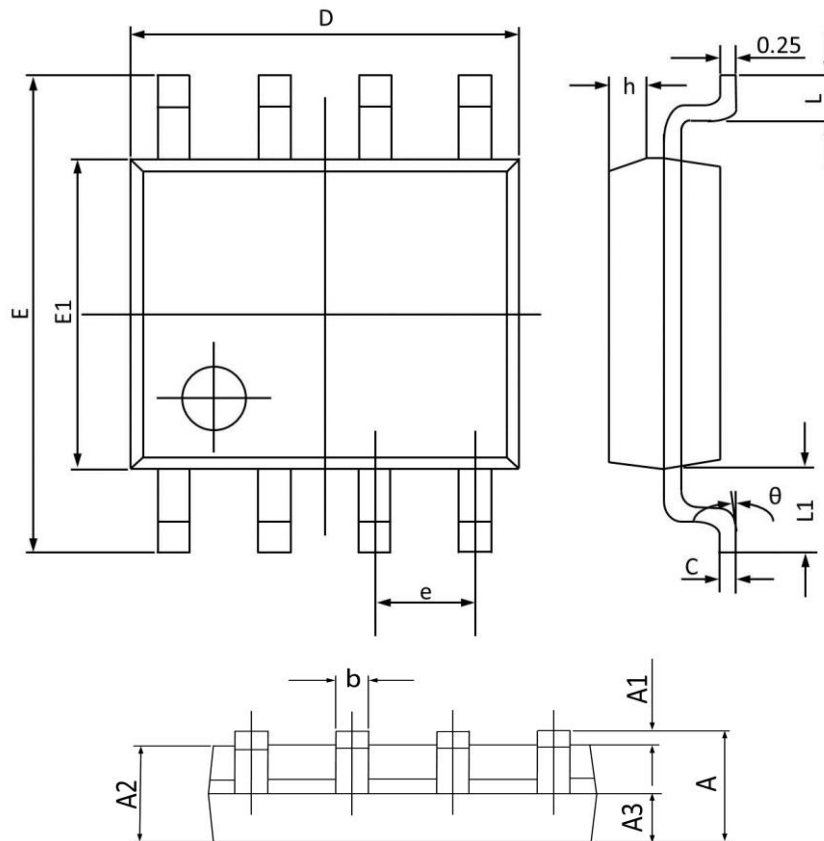


Fig.12 Gate Charge Waveform

SOP8 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.800	0.053	0.069
A1	0.050	0.250	0.002	0.010
A2	1.250	1.650	0.049	0.065
A3	0.500	0.700	0.020	0.028
b	0.300	0.510	0.012	0.020
c	0.150	0.260	0.006	0.010
D	4.700	5.100	0.185	0.201
E	5.800	6.200	0.228	0.244
E1	3.700	4.100	0.146	0.161
e	1.270(BSC)		0.050(BSC)	
h	0.250	0.500	0.010	0.020
L	0.400	1.000	0.016	0.039
L1	1.050(BSC)		0.041(BSC)	
θ	0°	8°	0°	8°